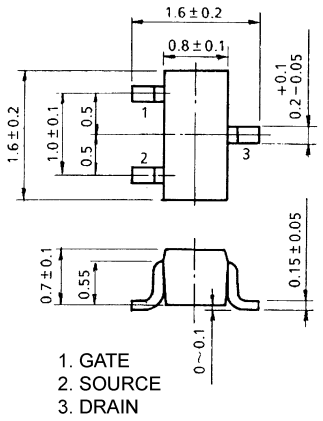
TOSHIBA Field-Effect Transistor Silicon N-Channel MOS Type

SSM3K35FS

○ High-Speed Switching Applications
○ Analog Switch Applications

- 1.2-V drive
- Low ON-resistance: R_{on} = 20 Ω (max) (@V_{GS} = 1.2 V)
  : R_{on} = 8 Ω (max) (@V_{GS} = 1.5 V)
  : R_{on} = 4 Ω (max) (@V_{GS} = 2.5 V)
  : R_{on} = 3 Ω (max) (@V_{GS} = 4.0 V)

Unit: mm



SSM	
JEDEC	-
JEITA	-
TOSHIBA	2-2H1B

Weight: 2.4 mg (typ.)

Absolute Maximum Ratings (Ta = 25˚C)

Characteristic		Symbol	Rating	Unit
Drain–source voltage		V_{DSS}	20	V
Gate–source voltage		V_{GSS}	±10	V
Drain current	DC	I_D	180	mA
	Pulse	I_{DP}	360	
Drain power dissipation		P_D	100	mW
Channel temperature		T_{ch}	150	°C
Storage temperature		T_{stg}	−55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

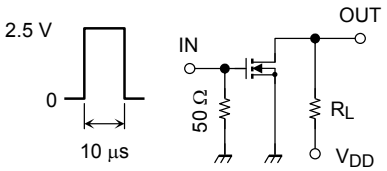
Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±10 V, V_{DS} = 0V	—	—	±10	μA
Drain–source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 0.1 mA, V_{GS} = 0V	20	—	—	V
Drain cutoff current		I_{DSS}	V_{DS} = 20 V, V_{GS} = 0V	—	—	1	μA
Gate threshold voltage		V_{th}	V_{DS} = 3 V, I_D = 1 mA	0.4	—	1.0	V
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = 3 V, I_D = 50 mA (Note 1)	115	—	—	mS
Drain–source ON-resistance		$R_{DS\ (ON)}$	I_D = 50 mA, V_{GS} = 4 V (Note 1)	—	1.5	3	Ω
			I_D = 50 mA, V_{GS} = 2.5 V (Note 1)	—	2	4	
			I_D = 5 mA, V_{GS} = 1.5 V (Note 1)	—	3	8	
			I_D = 5 mA, V_{GS} = 1.2 V (Note 1)	—	5	20	
Input capacitance		C_{iss}	V_{DS} = 3 V, V_{GS} = 0V, f = 1 MHz	—	9.5	—	pF
Reverse transfer capacitance		C_{rss}		—	4.1	—	
Output capacitance		C_{oss}		—	9.5	—	
Switching time	Turn-on time	t_{on}	V_{DD} = 3 V, I_D = 50 mA, V_{GS} = 0 to 2.5 V	—	115	—	ns
	Turn-off time	t_{off}		—	300	—	
Drain–source forward voltage		V_{DSF}	I_D = - 180 mA, V_{GS} = 0V (Note 1)	—	-0.9	-1.2	V

Note 1: Pulse test

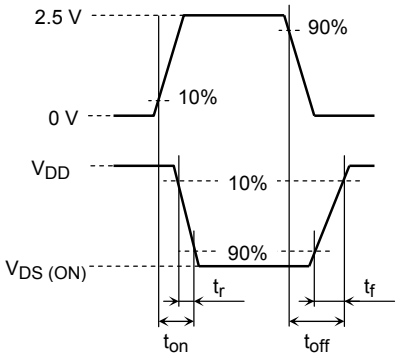
Switching Time Test Circuit

(a) Test Circuit



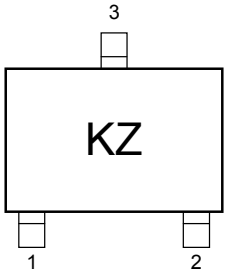
V_{DD} = 3 V
D.U. ≤ 1%
V_{IN}: t_r, t_f < 5 ns
(Z_{out} = 50 Ω)
Common Source
Ta = 25°C

(b) V_{IN}

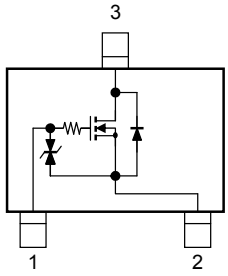


(c) V_{OUT}

Marking



Equivalent Circuit (top view)



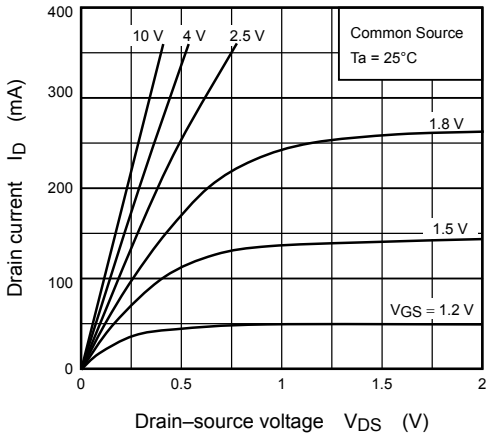
Usage Considerations

Let V_{th} be the voltage applied between gate and source that causes the drain current (I_D) to below (1 mA for the SSM3K35FS). Then, for normal switching operation, $V_{GS(on)}$ must be higher than V_{th}, and $V_{GS(off)}$ must be lower than V_{th}. This relationship can be expressed as: $V_{GS(off)} < V_{th} < V_{GS(on)}$.
Take this into consideration when using the device.

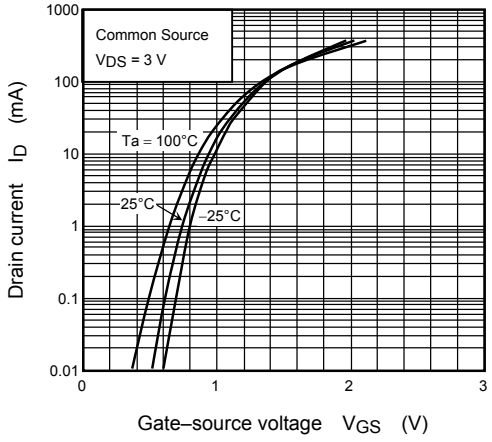
Handling Precaution

When handling individual devices (which are not yet mounting on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

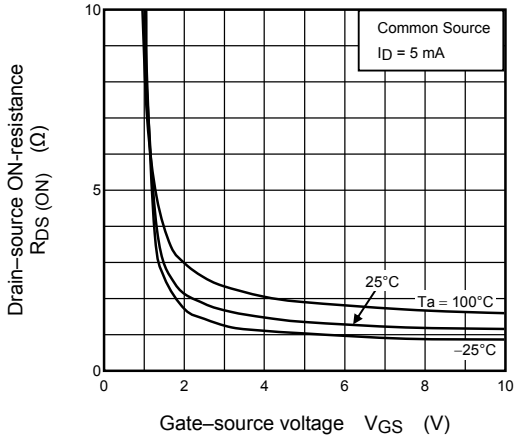
$I_D - V_{DS}$



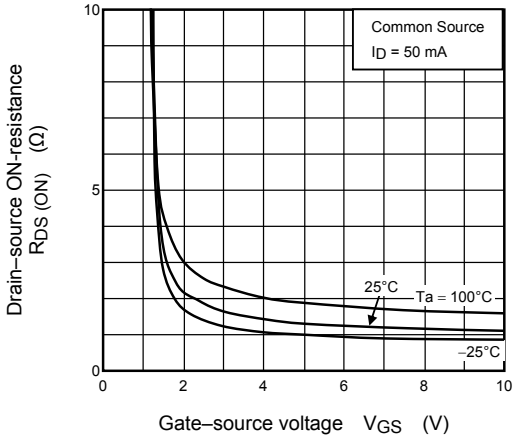
$I_D - V_{GS}$



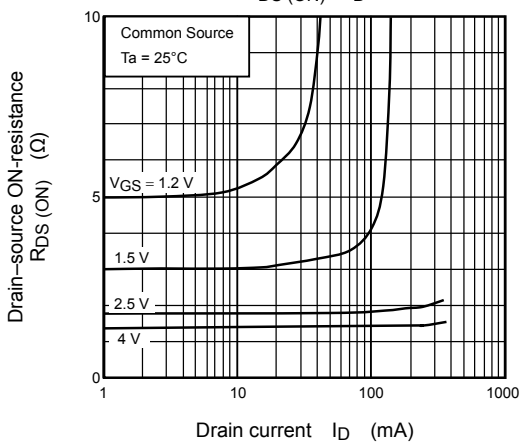
$R_{DS\ (ON)} - V_{GS}$



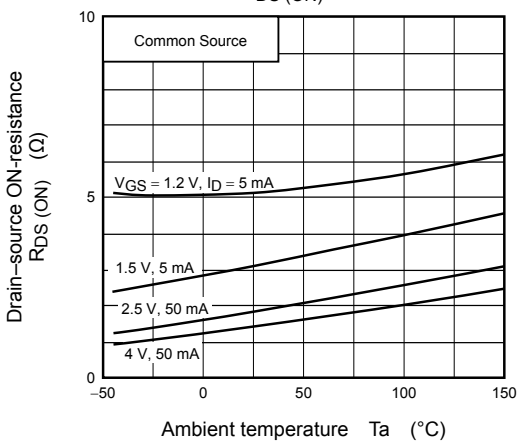
$R_{DS\ (ON)} - V_{GS}$



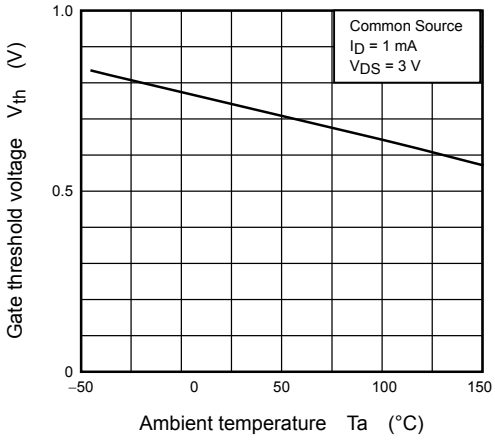
$R_{DS\ (ON)} - I_D$



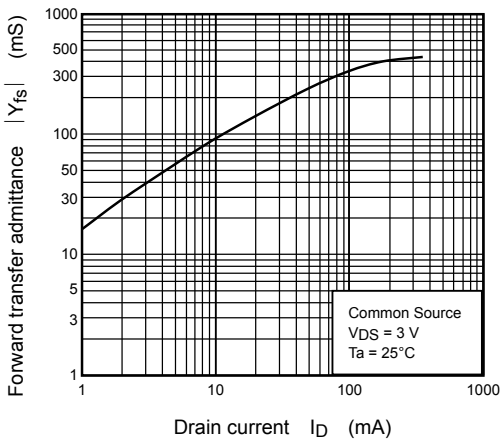
$R_{DS\ (ON)} - Ta$



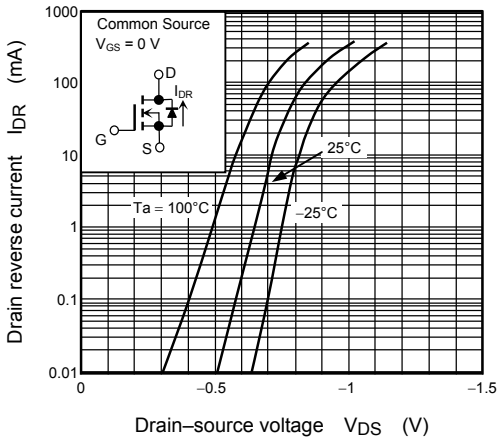
V_{th} – Ta



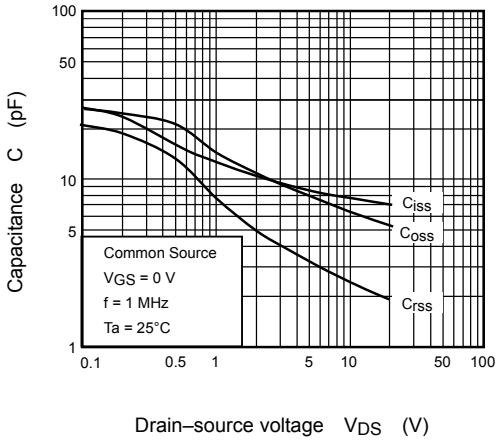
$|Y_{fs}|$ – I_D



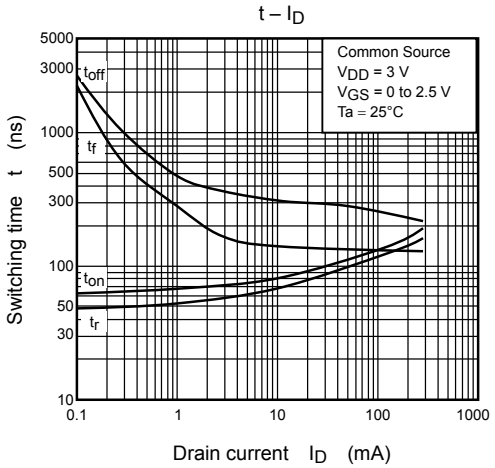
I_{DR} – V_{DS}



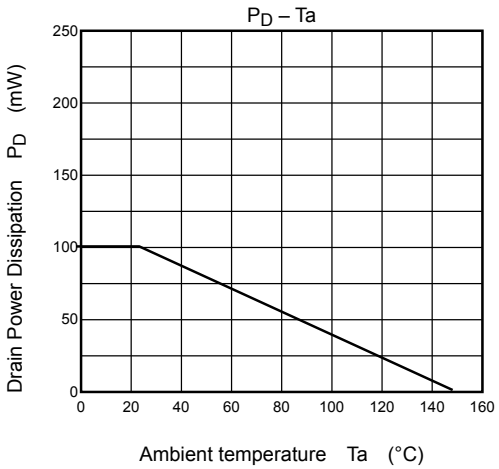
C – V_{DS}



t – I_D



P_D – Ta



RESTRICTIONS ON PRODUCT USE

20070701-EN GENERAL

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